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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Luca G. Fasoli, et al.

Title: MEMORY ARRAY INCORPORATING MEMORY CELLS ARRANGED  
IN NAND STRINGS

Application No.: 10/729,843

Filed: December 5, 2003

Examiner: Luu, Pho M.

Group Art Unit: 2824

Atty. Docket No.: 023-0031

Confirmation No.: 8321

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March 15, 2005

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**INFORMATION DISCLOSURE STATEMENT**  
**37 C.F.R. § 1.97(b)**

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, § 1.97 and § 1.98, the undersigned brings to the Examiner's attention in the above-identified application the patents, publications, applications or other information identified in the attached:

- Form(s) PTO/SB/08A (5 page(s), with copy of 4 reference(s)).
- Form(s) PTO/SB/08B (2 page(s), with copy of 20 reference(s)).
- Listing of Pending Applications (1 page(s), with copy of no application(s)).
- Other: N/A

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For each item of information listed that is not in the English language, the undersigned has provided a concise explanation of the relevance through (i) an English language abstract, (ii) an English language equivalent application, or (iii) if cited in a search report or other action by a foreign patent office in a counterpart foreign application, an English language version of the search report or action that indicates the degree of relevance found by the foreign office.

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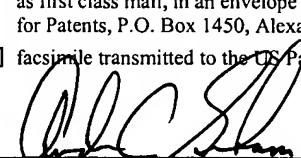
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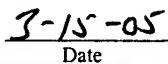
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Andrew C. Graham


  
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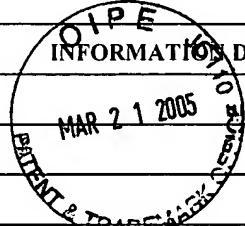
Respectfully submitted,



Andrew C. Graham, Reg. No. 36,531  
 Attorney for Applicant(s)  
 (512) 338-6313  
 (512) 338-6301 (fax)

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PTO/SB/08A (Substitute for form 1449/PTO)	Attorney Docket No.: 023-0031
	Application No.: 10/729,843
<b>O P E INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>	First Named Inventor: Luca G. Fasoli et al.
<i>MAR 21 2005</i>	Filing Date: December 5, 2003
	Group Art Unit: 2824
	Examiner Name: Pho M. Luu
Sheet 1 of 5	Date Submitted: March 15, 2005



U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	4,142,176	02-27-1979	Dozier	
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	AN	JA 62-142363	06-25-1987		
	AO	JA 62-155568	07-10-1987		
	AP	JA-2001-358237	12-26-2001		
	AQ	JA-2002-280467	09-27-2002		
Examiner Signature				Date Considered	

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<sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

PTO/SB/08A (Substitute for form 1449/PTO)	Attorney Docket No.: 023-0031
	Application No.: 10/729,843
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>	First Named Inventor: Luca G. Fasoli et al.
(Continuation Sheet)	Filing Date: December 5, 2003
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	BE					
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	BV					
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	BZ	6,515,888	02-04-2003	Johnson et al.	
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	CN					
	CO					
	CP					
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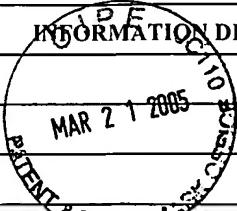
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	DB				
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	DD					
	DE					
	DF					
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#### NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	AA	DURISETY, CHANDRA SEKHAR ACHARYULU, "Analysis and Characterization of Single-Poly Floating Gate Devices in 0.35um PDSOI Process", A Thesis Presented for the Master of Science Degree, The University of Tennessee, Knoxville, December 2002, pp. i-viii and 1-80.	
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Examiner Signature		Date Considered	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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### NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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